

TENTATIVE

TOSHIBA PHOTOCOUPLER GaAs IRED + PHOTO-TRIAC

TLP762J

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
TRIAC DRIVER
SOLID STATE RELAY

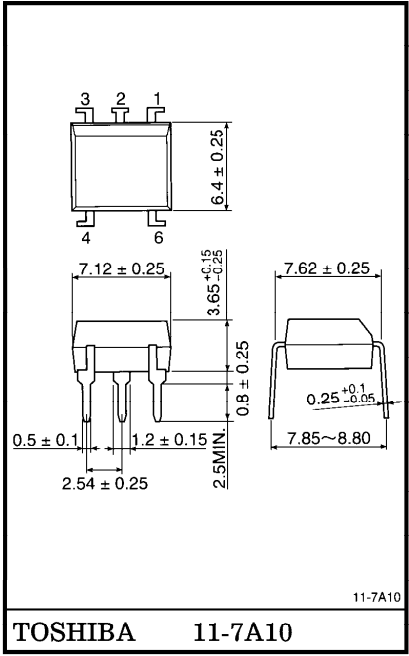
The TOSHIBA TLP762J consists of a GaAs infrared LED optically coupled to a photo-triac in a 6 lead plastic DIP.

- Peak Off-State Voltage : 600V (MIN.)
- Trigger LED Current : 10mA (MAX.)
- On-State Current : 100mA (MAX.)
- Isolation Voltage : 4000Vrms (MIN.)
- UL Recognized : UL1577, File No. E67349
- BSI Approved : BS EN60065 : 1994,
Certificate No. 7831
BS EN60950 : 1992,
Certificate No. 7832
- SEMKO Approved : SS EN60065 (EN60065, 1993)
SS EN60950 (EN60950, 1992)
SS EN60335 (EN60335, 1988)
Certificate No. 9522145
- Option (D4) type
VDE Approved : DIN VDE0884 / 06.92
Certificate No. 91803
Maximum Operating Insulation Voltage : 890V_{PK}
Highest Permissible Over Voltage : 6000V_{PK}

(Note) When a VDE0884 approved type is needed,
please designate the “Option (D4)”

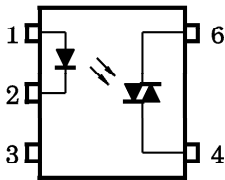
	7.62mm pich	10.16mm pich
	TLP762J type	TLP762JF type
• Creepage Distance	: 7.0mm (Min.)	8.0mm (Min.)
Clearance	: 7.0mm (Min.)	8.0mm (Min.)
Internal Creepage Path	: 4.0mm (Min.)	4.0mm (Min.)
Insulation Thickness	: 0.5mm (Min.)	0.5mm (Min.)

Unit in mm



Weight : 0.42g

PIN CONFIGURATION (TOP VIEW)



- 1 : ANODE
- 2 : CATHODE
- 3 : N.C.
- 4 : TRIAC 1
- 6 : TRIAC 2

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT
LED	Forward Current		I _F	50	mA
	Forward Current Derating (Ta≥ 53°C)		ΔI _F / °C	−0.7	mA / °C
	Peak Forward Current (100μs pulse, 100pps)		I _{FP}	1	A
	Reverse Voltage		V _R	5	V
	Junction Temperature		T _j	125	°C
DETECTOR	Off-State Output Terminal Voltage		V _{DRM}	600	V
	On-State RMS Current	Ta = 25°C	I _T (RMS)	100	mA
		Ta = 70°C		50	
	On-State Current Derating (Ta = ≥ 25°C)		ΔI _T / °C	−1.1	mA / °C
	Peak On-State Current (100μs pulse, 120pps)		I _{TP}	2	A
	Peak Nonrepetitive Surge Current (PW = 10ms, DC = 10%)		I _{TSM}	1.2	A
	Junction Temperature		T _j	115	°C
	Storage Temperature Range		T _{stg}	−55~125	°C
	Operating Temperature Range		T _{opr}	−40~100	°C
	Lead Soldering Temperature (10s)		T _{sol}	260	°C
Isolation Voltage (AC, 1 min., R.H. ≤ 60%)		BV _S	4000	V _{rms}	

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{AC}	—	—	240	V _{ac}
Forward Current	I _F	15	20	25	mA
Peak On-State Current	I _{TP}	—	—	1	A
Operating Temperature	T _{opr}	−25	—	85	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Peak Off-State Current	I_{DRM}	$V_{\text{DRM}} = 600\text{V}$	—	10	1000	nA
	Peak On-State Voltage	V_{TM}	$I_{\text{TM}} = 100\text{mA}$	—	1.7	3.0	V
	Holding Current	I_H	—	—	0.6	—	mA
	Critical Rate of Rise of Off-State Voltage	dv/dt	$V_{\text{in}} = 240\text{V}, T_a = 85^\circ\text{C}$	—	500	—	$\text{V}/\mu\text{s}$
	Critical Rate of Rise of Commutating Voltage	$dv/dt (C)$	$I_T = 15\text{mA}$ $V_{\text{in}} = 60\text{V}_{\text{rms}}$	—	0.2	—	$\text{V}/\mu\text{s}$

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	I_{FT}	$V_T = 6\text{V}$	—	—	10	mA
Capacitance (Input to Output)	C_S	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance	R_S	$V_S = 500\text{V}$	1×10^{12}	10^{14}	—	Ω
Isolation Voltage	BV_S	AC, 1 minute	4000	—	—	V_{rms}
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V_{dc}

